

10 transistors for activating respective ones of said access
transistors [upon receipt of] in response to a selection
signal for selecting one of said memory cells[,]; and
15 a differential sense amplifier for reading from and
writing to said memory cells, said sense amplifier having a
first input connected to said bit line, and a second input
connected to receive a reference signal, said sense
amplifier having a data [input/output] input terminal and a
data output terminal, said sense amplifier for
20 differentially [driving] comparing signals on said first and
second input lines for reading a data state from a selected
one of said memory cells, [connected thereto] and for
applying [the] a data state [thus] read from said selected
memory cell to said [input/output] data output terminal, and
25 said sense amplifier for driving said bit [lines] line
connected to said selected memory cell to one of a set of
predetermined voltage states corresponding to a data state
received at said [input/output] data input terminal for
writing said received data state into the selected one of
said memory cells.

63. (Amended) A non-volatile memory circuit as recited in claim 61 including a respective complementary memory cell [for] associated with each memory cell of said plurality of memory cells, wherein [the] an output of the corresponding complementary memory cell is transmitted [through] by a bit line to provide said reference signal to said sense amplifier.

66. (Amended) A non-volatile memory cell as recited in claim 61 including a dummy ferroelectric capacitor memory cell [for] associated with said plurality of memory cells, and a bit line connected to provide [the] an output of the dummy memory cell as the reference signal to said sense amplifier.

67. (Amended) A non-volatile memory circuit, comprising:

5 a plurality of memory cells each [comprising] including
a ferroelectric capacitor connected in series with an access
transistor, said plurality of memory cells being connected
between a plurality of respective bit lines and a common
drive line,

10 a word line connected to control terminals of said
access transistors for activating said transistors [upon
receipt of] in response to a selection signal for selecting
one of said memory cells, and

15 a plurality of differential sense amplifiers
corresponding respectively to said bit lines for reading
from and writing to [said] memory cells associated with the
bit lines, each sense amplifiers having a first input
connected to the corresponding bit line and a second input
connected to receive a reference signal, each said sense
amplifier having a data input/output terminal, said sense
amplifiers for differentially [driving] comparing signals on
20 said first and second inputs thereof for reading a data
state from the one of said memory cells connected thereto,
and for applying [the] a data state [then] read from said
selected memory cell to said [input/output] output terminal,
and said sense amplifiers for driving the corresponding bit
25 lines connected to said memory cells to predetermined
voltage states corresponding to a data state received at
said [input/output] input terminal for writing said received
data state into the corresponding one of said memory cells.